PLANT FOR EPITAXIAL LAYERS OVERGROWTH WITH GROUP PLATES PROCESSING

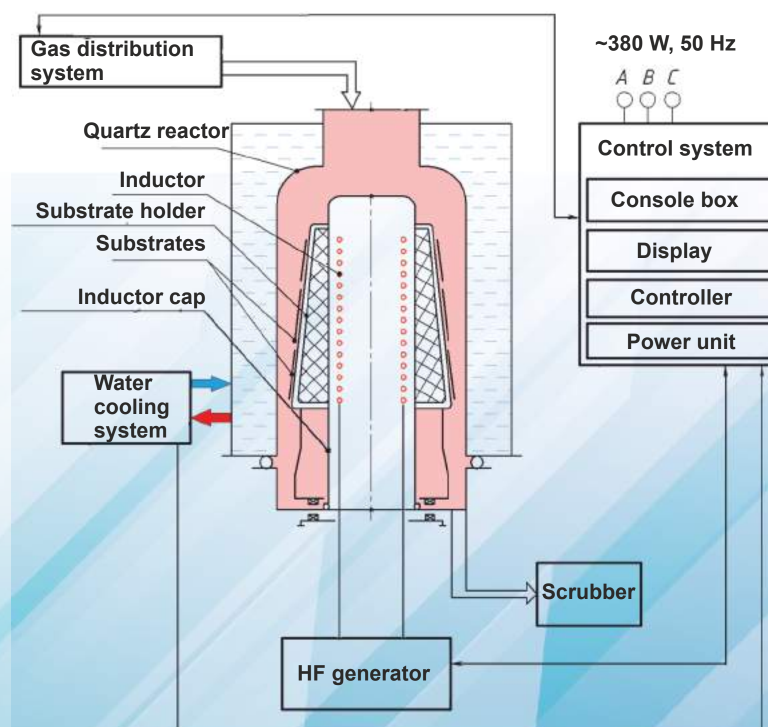
EPI ETM

Purpose:

Epitaxial deposition of silicon layers in a wide range of thicknesses and resistivity onto single-crystal silicon or sapphire wafers by chloride or chloride hydride deposition from the gas phase .

Special characteristics:

- Quartz horizontal slit-type reactor with controlled gas dynamics;
- Ø 100, 150, 200 mm substrate loading;
- IR heating with a temperature control of 5 areas;
- Microprocessing control system;
- Consumed power not more than 70kW;
- 10 m^2 area per one plant.



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